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60V N-Channel Power MOSFET



PDFN56

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Pin Definition:

Source
 Source
 Drain
 Source
 Drain
 Gate

Note:

MSL 1 (Moisture Sensitivity Level) per J-STD-020

Key Parameter Performance

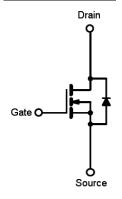
Parameter		Value	Unit	
V_{DS}		60 V		
R _{DS(on)} (max)	V _{GS} = 10V	23	mΩ	
	V _{GS} = 4.5V	28		
Q_{g}		28	nC	

Ordering Information

Part No.	Package	Packing		
TSM230N06PQ56 RLG	PDFN56	2.5kpcs / 13" Reel		

Note: Halogen-free according to IEC 61249-2-21 definition

Block Diagram



N-Channel MOSFET

Absolute Maximum Ratings (Tc = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	60	V
Gate-Source Voltage		V _{GS}	±20	V
Ocation and Ducin Comment	Tc = 25°C		44	Α
Continuous Drain Current	Tc = 100°C	l _D	28	Α
Pulsed Drain Current (Note 1)		I _{DM}	176	Α
Single Pulse Avalanche Energy (Note 2)		E _{AS}	42	mJ
Power Dissipation @ T _C = 25°C		P _D	83	W
Operating Junction Temperature		T _J	-55 to +150	°C
Storage Temperature Range		T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Case	R _{eJC}	1.5	00.004	
Thermal Resistance - Junction to Ambient	R _{eJA}	62	°C/W	



60V N-Channel Power MOSFET



Electrical Specifications (T_C = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static				<u>'</u>		
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	60			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 20A$	R _{DS(on)}		20	23	mΩ
	$V_{GS} = 4.5V, I_D = 12A$			23	28	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.2	1.8	2.5	V
	$V_{DS} = 60V, V_{GS} = 0V$				1	μΑ
Zero Gate Voltage Drain Current	V _{DS} = 48V, T _J = 125°C	I_{DSS}			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 10A$	g _{fs}		9		S
Dynamic				l		
Total Gate Charge (Note 3,4)		Q_g		28		nC
Gate-Source Charge (Note 3,4)	$V_{DS} = 30V, I_D = 15A,$ $V_{GS} = 10V$	Q_{gs}		3.5		
Gate-Drain Charge (Note 3,4)		Q_{gd}		6.5		
Input Capacitance		C _{iss}		1680		pF
Output Capacitance	$V_{DS} = 20V, V_{GS} = 0V,$	C _{oss}		115		
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		85		
Switching						
Turn-On Delay Time (Note 3,4)		$t_{d(on)}$		7.2		ns
Turn-On Rise Time (Note 3,4)	$V_{DD} = 30V, I_{D} = 1A,$	t _r		38		
Turn-Off Delay Time (Note 3,4)	$V_{GS} = 10V, R_G = 6\Omega$	t _{d(off)}		34		
Turn-Off Fall Time (Note 3,4)		t _f		8.2		
Source-Drain Diode Ratings and Ch	aracteristic					
Maximum Continuous Drain-Source		ı			44	Α
Diode Forward Current	Integral reverse diode in the MOSFET	I _S			44	
Maximum Pulse Drain-Source Diode		I _{SM}			176	Α
Forward Current						
Diode-Source Forward Voltage (Note 3)	$V_{GS} = 0V$, $I_S = 1A$	V _{SD}			1	V
Reverse Recovery Time (Note 3)	$V_{GS} = 0V, I_{S} = 1A$ $dI_{F}/dt = 100A/\mu s$	t _{rr}		19.6		ns
Reverse Recovery Charge (Note 3)	uif/ut = 100A/μS	Q _{rr}		14.2		nC

Note:

- 1. Pulse width limited by safe operating area
- 2. $L=0.1mH,\ I_{AS}=29A,\ V_{DD}=25V,\ R_G=25\Omega,\ Starting\ T_J=25^{\circ}C$
- 3. Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 4. Switching time is essentially independent of operating temperature.

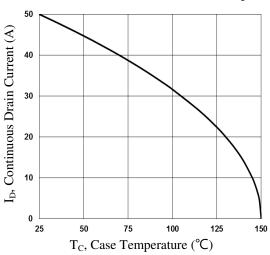


60V N-Channel Power MOSFET



Electrical Characteristics Curve

Continuous Drain Current vs. Tc



R_{DS(on)}, On Resistance (mΩ) 31 VGS=10V

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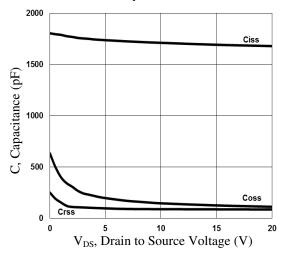
R_{DS(on)} vs. Continuous Drain Current

I_D, Continuous Drain Current (A)

29

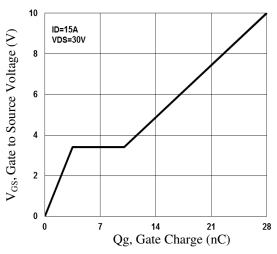
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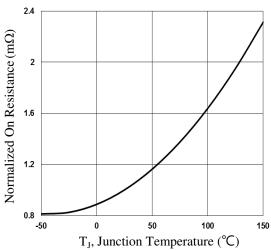




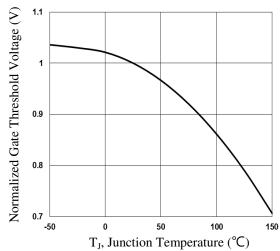
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On-Resistance vs. Junction Temperature



Threshold Voltage vs. Junction Temperature



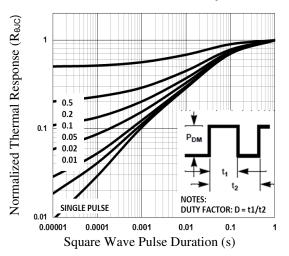


60V N-Channel Power MOSFET

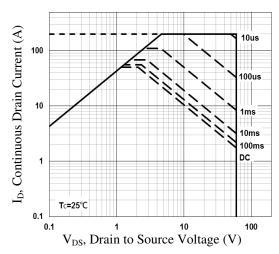


Electrical Characteristics Curve

Normalized Thermal Transient Impedance Curve



Maximum Safe Operating Area

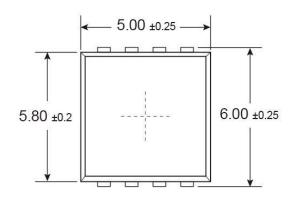


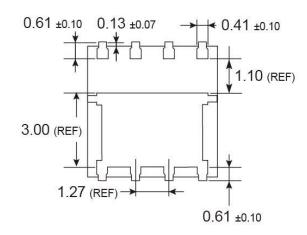


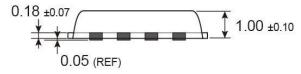
60V N-Channel Power MOSFET



PDFN56 Mechanical Drawing







Unit: Millimeters

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)

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L = Lot Code

Version: B1710



Pb ROHS

TSM230N06PQ56 60V N-Channel Power MOSFET

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